

General Description

The WSD4062DN56 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications . The WSD4062DN56 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

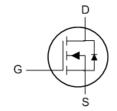
BVDSS	RDSON	ID
40V	7.0mΩ	62A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

DFN5X6-8L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V	62	Α
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V	29	Α
I _{DM}	Pulsed Drain Current ^a	60	А
EAS Single Pulse Avalanche Energy ^b		42	mJ
I _{AS}	I _{AS} Avalanche Current		Α
P _D @T _a =25℃	P _D @T _a =25℃ Total Power Dissipation		W
T _{STG}	T _{STG} Storage Temperature Range -		$^{\circ}$
T _J Operating Junction Temperature Range -55 to		-55 to 150	${\mathbb C}$

Thermal Data

Symbol	bol Parameter		Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		60	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		3.9	°C/W

Note a: Package is limited to 60A.

Note b: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature Tj=25°C).



Electrical Characteristics ($T_J=25$ \subset , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient Reference to 25°C , I _D =1mA			0.043		V/℃
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A		7.0	10.5	mΩ
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =15A		9.0	13.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	-V _{GS} =V _{DS} , I _D =250uA	1.5	1.8	2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} -V _{DS} , I _D -250UA		-6.94		mV/℃
la co	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25℃			2	uA
I _{DSS}	Dialii-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =55℃			10	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance V _{DS} =5V , I _D =20A			33		S
R_g	Gate Resistance V _{DS} =0V , V _{GS} =0V , f=1MHz			1.1	2	Ω
Q_g	Total Gate Charge (10V)			76	91	
Q _{gs}	Gate-Source Charge	V_{DS} =20V , V_{GS} =10V , I_{D} =40A		12	14.4	nC
Q_{gd}	Gate-Drain Charge			15.5	18.6	
T _{d(on)}	Turn-On Delay Time			12	16	
T _r	Rise Time	V_{DD} =30V , V_{GEN} =10V , R_{G} =1 Ω ,		9	12	no
T _{d(off)}	Turn-Off Delay Time	I_D =1A ,RL=15 Ω .		25	32	ns
T _f	Fall Time			6	9	
C _{iss}	Input Capacitance			1150		
C _{oss}	Output Capacitance	V _{DS} =20V , V _{GS} =0V , f=1MHz		140		pF
C _{rss}	Reverse Transfer Capacitance			90		

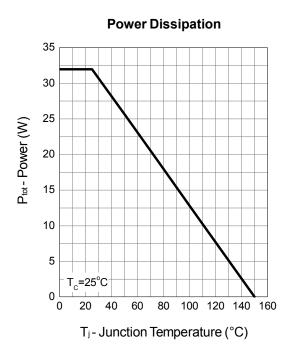
Diode Characteristics

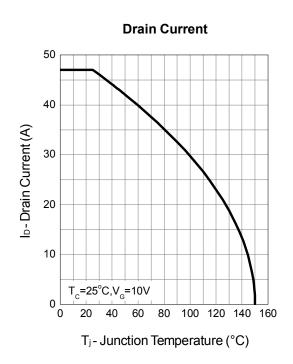
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			20	Α
I _{SM}	Pulsed Source Current ^{2,6}	VG-VD-UV, FOICE Cullent			60	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =20A , T _J =25℃			1.3	V

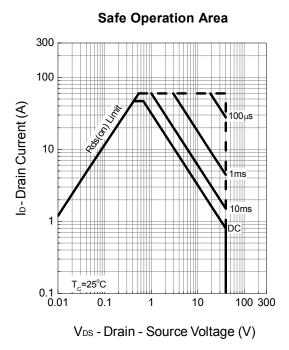
Note

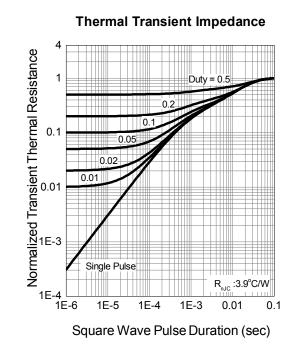
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec .
- 2.The data tested by pulsed , pulse width $\, \leqq \,$ 300us , duty cycle $\, \leqq \,$ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.5mH,I_{AS}=13A
- 5. The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.
- 7. Package limitation current is 60A.



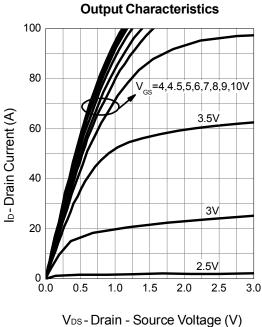


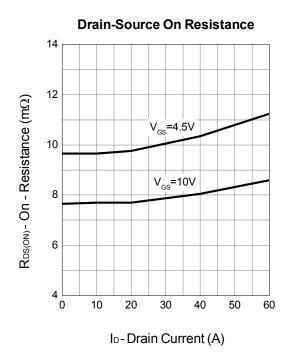


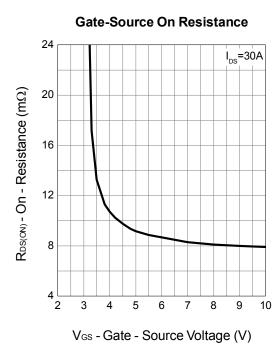


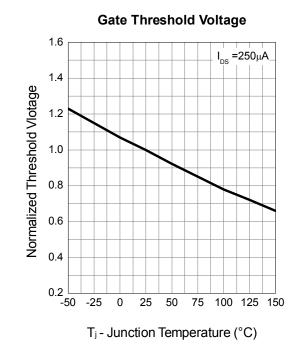






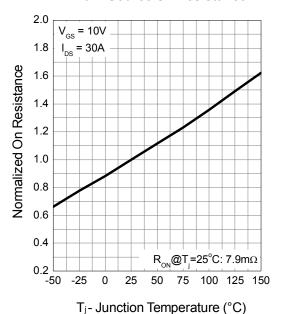




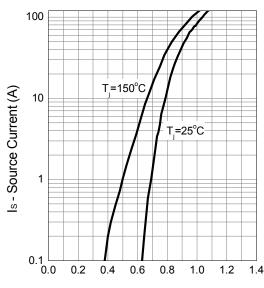




Drain-Source On Resistance

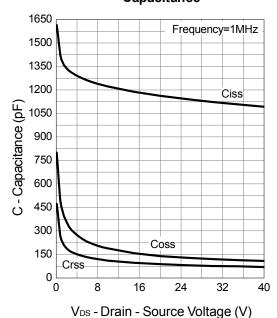


Source-Drain Diode Forward

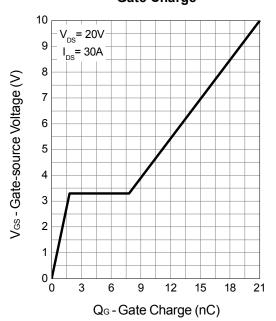


Vsp - Source - Drain Voltage (V)

Capacitance

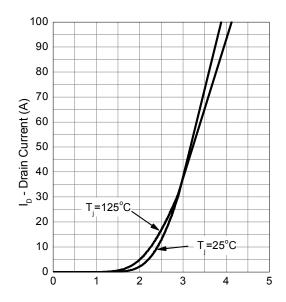


Gate Charge





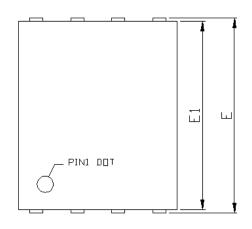
Transfer Characteristics

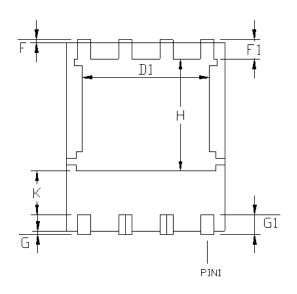


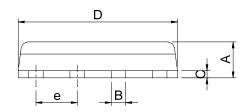
 $V_{_{GS}}$ - Gate-Source Voltage (V)



Package DFN5x6-8L





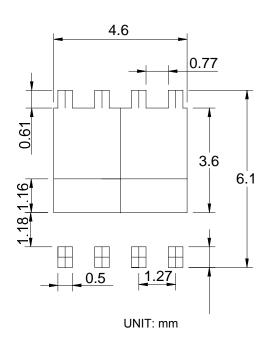


Ş					
SYMBOL	MILLIMETERS		INCHES		
6	MIN.	MAX.	MIN.	MAX.	
Α	0.90	1.20	0.035	0.047	
В	0.3	0.51	0.012	0.020	
С	0.19	0.25	0.007	0.010	
D	4.80	5.30	0.189	0.209	
D1	3.6	4.40	0.141	0.173	
E	5.90	6.20	0.232	0.244	
E1	5.50	5.80	0.217	0.228	
е	1.27	BSC	0.050 BSC		
F	0.05	0.30	0.002	0.012	
F1	0.35	0.75	0.014	0.030	
G	0.05	0.30	0.002	0.012	
G1	0.35	0.75	0.014	0.030	
Н	3.34	3.9	0.131	0.154	
K	0.762	-	0.03	-	

Note : 1.Dimension D, D1 and E1 do not include mold flash or protrusions.

Mold flash or protrusions shall not exceed 10 mil.

RECOMMENDED LAND PATTERN





Attention

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5,In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.
- 9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Winsok manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3